优尚

YOUSHANG SEMICONDUCTOR

设计研发新型功率器件

各类小信号开关

中低压及高压大电流等场效应管

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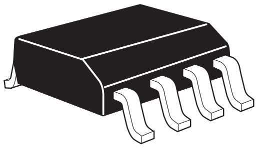
SUMMARY

$V_{(BR)DSS}$ = -30V; $R_{DS(ON)}$ = 0.045Ω; I_D= -5.5A

DESCRIPTION

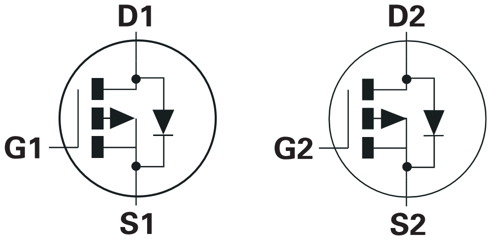
This new generation of trench MOSFETs from Zetex utilizes a unique structure that combines the benefits of low on-resistance with fast switching speed. This makes them ideal for high efficiency, low voltage, power management applications.



SO8

FEATURES

- Low on-resistance
- Fast switching speed
- Low threshold
- Low gate drive
- Low profile SOIC package



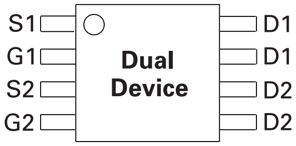
APPLICATIONS

- Motor Drive
- LCD backlighting

ORDERING INFORMATION

DEVICE	REEL	TAPE WIDTH	QUANTITY PER REEL
NK-ZXMP3A16DN8TA	7''	12mm	500 units
NK-ZXMP3A16DN8TC	13''	12mm	2500 units

PINOUT



Top view

DEVICE MARKING

NK-ZXMP
3A16

ABSOLUTE MAXIMUM RATINGS

PARAMETER	SYMBOL	LIMIT	UNIT
Drain-Source Voltage	V_{DSS}	-30	V
Gate-Source Voltage	V_{GS}	±20	V
Continuous Drain Current@V_{GS}=10V; T_A=25°C (b)(d) @V_{GS}=10V; T_A=70°C (b)(d) @V_{GS}=10V; T_A=25°C (a)(d)	I_D	-5.5 -4.4 -4.2	A A A
Pulsed Drain Current (c)	I_{DM}	-20	A
Continuous Source Current (Body Diode)(b)	I_S	-3.2	A
Pulsed Source Current (Body Diode)(c)	I_{SM}	-20	A
Power Dissipation at T_A=25°C (a)(d) Linear Derating Factor	P_D	1.25 10	W mW/°C
Power Dissipation at T_A=25°C (a)(e) Linear Derating Factor	P_D	1.8 14	W mW/°C
Power Dissipation at T_A=25°C (b)(d) Linear Derating Factor	P_D	2.1 17	W mW/°C
Operating and Storage Temperature Range	T_j:T_{stg}	-55 to +150	°C

THERMAL RESISTANCE

PARAMETER	SYMBOL	VALUE	UNIT
Junction to Ambient (a)(d)	$R_{\theta JA}$	100	°C/W
Junction to Ambient (b)(e)	$R_{\theta JA}$	70	°C/W
Junction to Ambient (b)(d)	$R_{\theta JA}$	60	°C/W

Notes

(a) For a dual device surface mounted on 25mm x 25mm FR4 PCB with coverage of single sided 1oz copper in still air conditions.

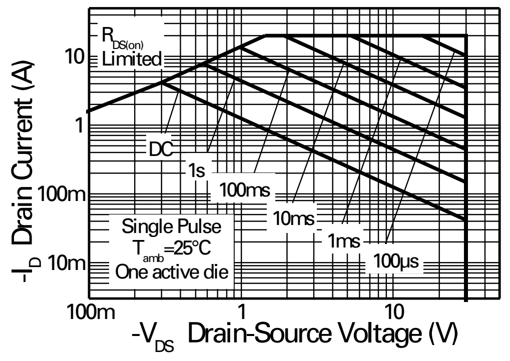
(b) For a dual device surface mounted on FR4 PCB measured at t ≤10 sec.

(c) Repetitive rating 25mm x 25mm FR4 PCB, D=0.05 pulse width=10μs - pulse width limited by maximum junction temperature.

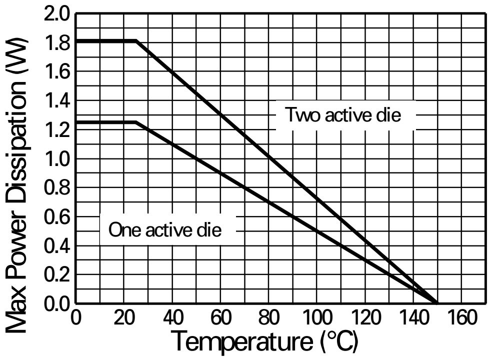
(d) For a dual device with one active die.

(e) For dual device with 2 active die running at equal power.

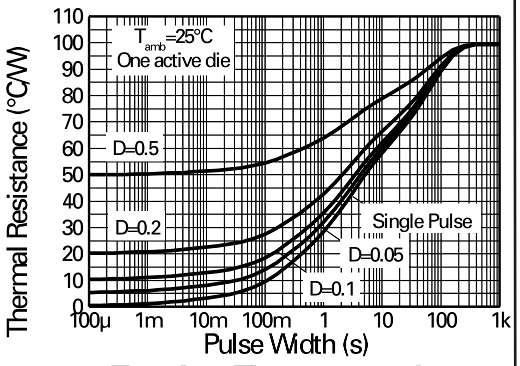
CHARACTERISTICS



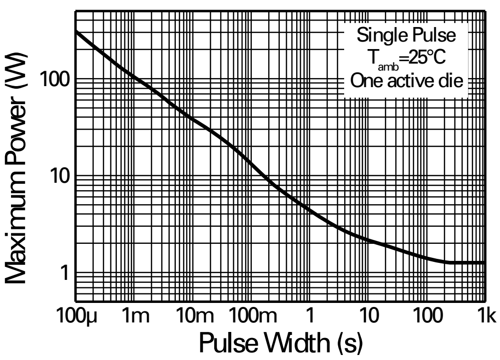
Safe Operating Area



Derating Curve



Transient Thermal Impedance



Pulse Power Dissipation

ELECTRICAL CHARACTERISTICS (at T_{amb} = 25°C unless otherwise stated)

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS
STATIC						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	-30			V	I_D=-250μA, V_{GS}=0V
Zero Gate Voltage Drain Current	I_{DSS}			-1.0	μA	V_{DS}=-30V, V_{GS}=0V
Gate-Body Leakage	I_{GSS}			100	nA	V_{GS}=±20V, V_{DS}=0V
Gate-Source Threshold Voltage	$V_{GS(th)}$	-1.0			V	I_D=-250μA, V_{DS}= V_{GS}
Static Drain-Source On-State Resistance (1)	$R_{DS(on)}$			0.045 0.070	Ω Ω	V_{GS}=-10V, I_D=-4.2A V_{GS}=-4.5V, I_D=-3.4A
Forward Transconductance (1)(3)	g_{fs}		9.2		S	V_{DS}=-15V,I_D=-4.2A
DYNAMIC (3)						
Input Capacitance	C_{iss}		1022		pF	V_{DS}=-15 V, V_{GS}=0V, f=1MHz
Output Capacitance	C_{oss}		267		pF	
Reverse Transfer Capacitance	C_{rss}		229		pF	
SWITCHING (2) (3)						
Turn-On Delay Time	$t_{d(on)}$		3.8		ns	V_{DD} =-15V, I_D=-1A R_G=6.0Ω, V_{GS}=-10V
Rise Time	t_r		6.5		ns	
Turn-Off Delay Time	$t_{d(off)}$		37.1		ns	
Fall Time	t_f		21.4		ns	
Gate Charge	Q_g		17.2		nC	V_{DS}=-15V,V_{GS}=-5V, I_D=-4.2A
Total Gate Charge	Q_g		29.6		nC	V_{DS}=-15V,V_{GS}=-10V, I_D=-4.2A
Gate-Source Charge	Q_{gs}		2.8		nC	
Gate-Drain Charge	Q_{gd}		8.6		nC	
SOURCE-DRAIN DIODE						
Diode Forward Voltage (1)	V_{SD}		-0.85	-0.95	V	T_J=25°C, I_S=-3.6A, V_{GS}=0V
Reverse Recovery Time (3)	t_{rr}		21.7		ns	T_J=25°C, I_F=-2A, di/dt= 100A/μs
Reverse Recovery Charge (3)	Q_{rr}		16.1		nC	

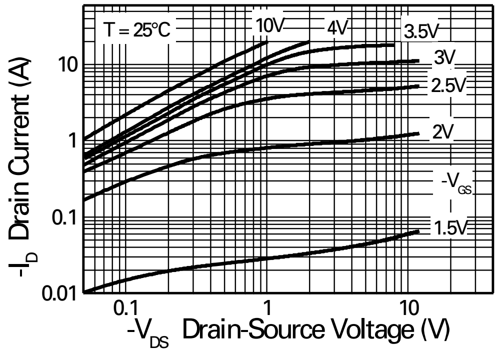
NOTES

(1) Measured under pulsed conditions. Width ≤300μs. Duty cycle ≤ 2% .

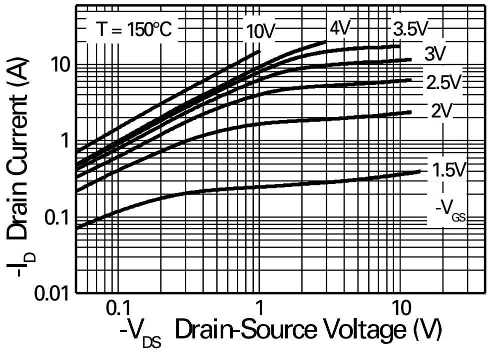
(2) Switching characteristics are independent of operating junction temperature.

(3) For design aid only, not subject to production testing.

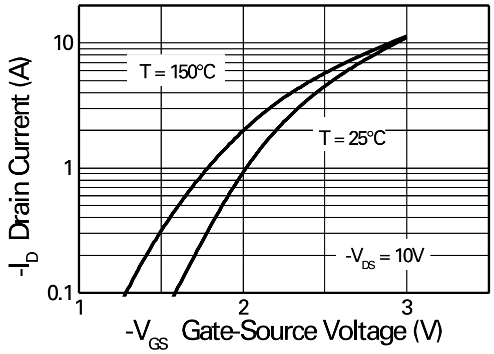
TYPICAL CHARACTERISTICS



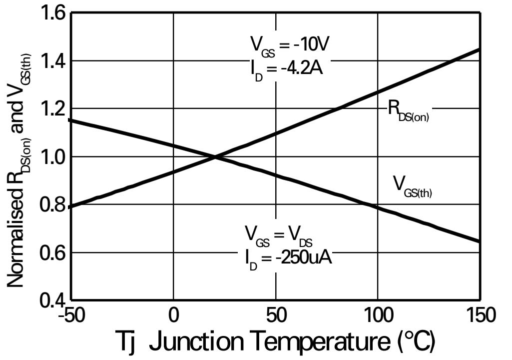
Output Characteristics



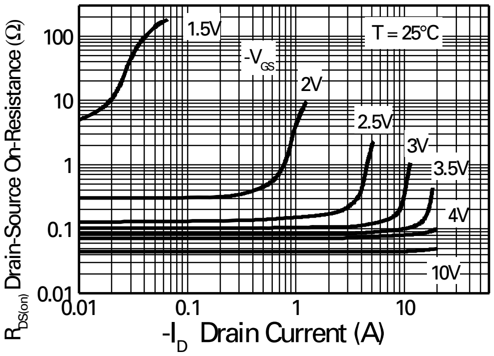
Output Characteristics



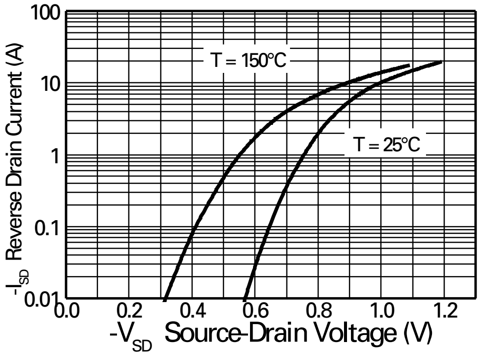
Typical Transfer Characteristics



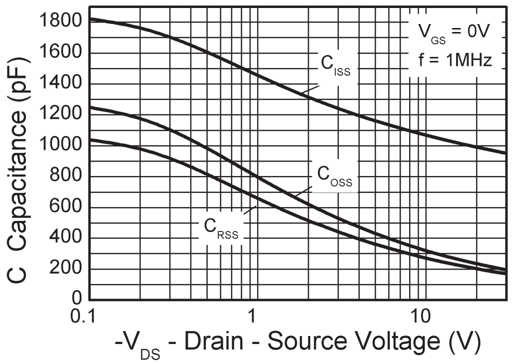
Normalised Curves v Temperature



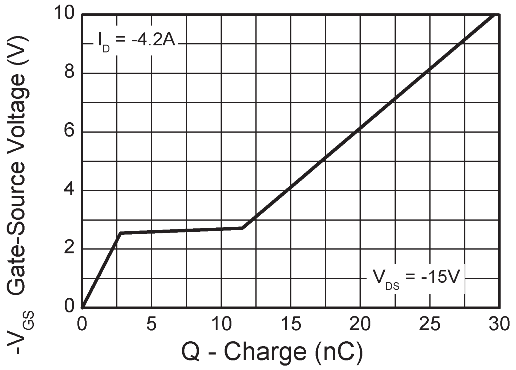
On-Resistance v Drain Current



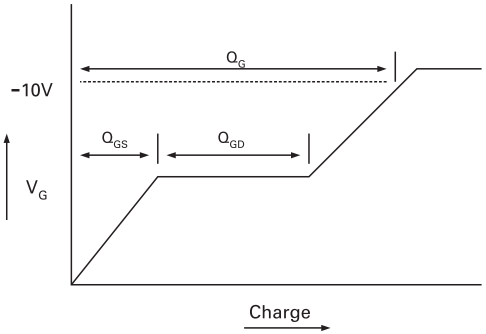
Source-Drain Diode Forward Voltage



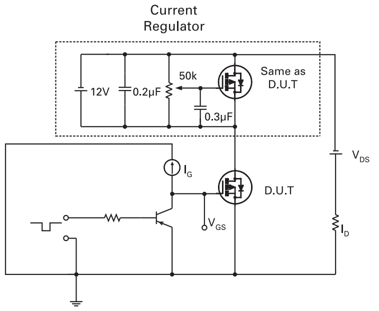
Capacitance v Drain-Source Voltage



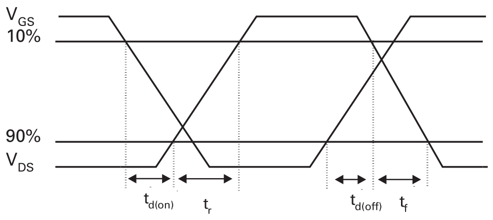
Gate-Source Voltage v Gate Charge



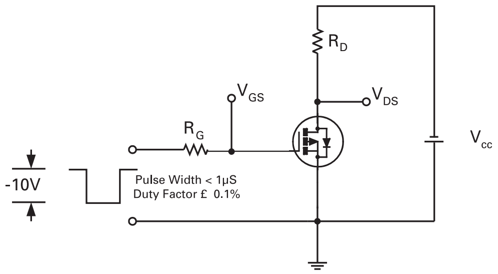
Basic Gate Charge Waveform



Gate Charge Test Circuit

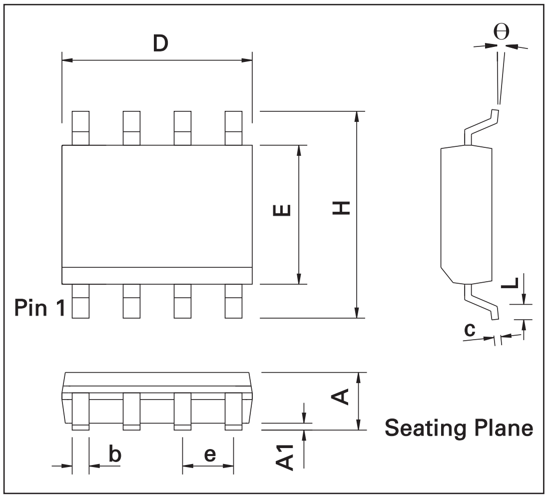


Switching Time Waveforms



Switching Time Test Circuit

PACKAGE OUTLINE



CONTROLLING DIMENSIONS ARE IN INCHES
APPROX IN MILLIMETRES

PACKAGE DIMENSIONS

DIM	Millimeters		Inches		DIM	Millimeters		Inches	
	Min	Max	Min	Max		Min	Max	Min	Max
A	1.35	1.75	0.053	0.069	e	1.27 BSC		0.050 BSC	
A1	0.10	0.25	0.004	0.010	b	0.33	0.51	0.013	0.020
D	4.80	5.00	0.189	0.197	c	0.19	0.25	0.008	0.010
H	5.80	6.20	0.228	0.244	Θ	0°	8°	0°	8°
E	3.80	4.00	0.150	0.157	h	0.25	0.50	0.010	0.020
L	0.40	1.27	0.016	0.050	-	-	-	-	-